Key Features

Frequency: 2.7-2.9GHz

Power Added Efficiency: 60% (typ)

Typical Gain: 12dB (typ)

Offset：50V

Typical Output: ≥57dBm

Packaging Mode: Cermet

Introduction

ER-GN2729-P57 is 2.7-2.9GHz high power and efficiency GaN IMFET, using GaN HEMT technology. It works with dual power supply, Vds=50V，and can provide 57dBm output power in 2.7-2.9GHz，typical power gain is 12dB， power added efficiency is 60% .

Maximum Ratings (TA=25℃)

Symbol	Parameter	Value	Mark
Vd	Drain Voltage	60V	
Vg	Gate Voltage	-5V	
Tch	Channel Temperature	150℃	[1]
Tstg	Storage Temperature	-65～150℃	

[1] Higher than any values above may cause permanent damage.

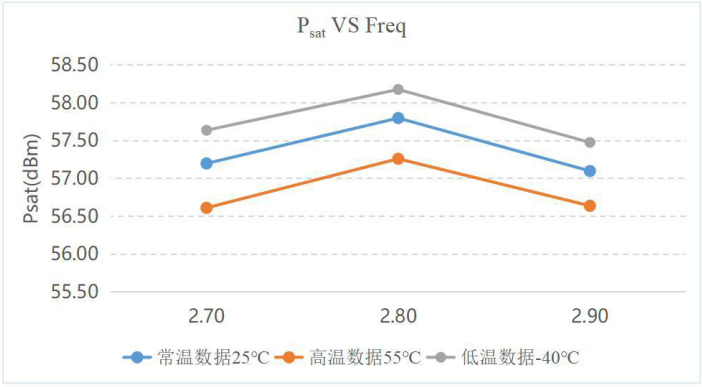
Specifications (T_A=25℃)

Symbol	Parameter	Values			Unit
		Min	Typ	Max	
Pout	Output Power	57		-	dBm
Id	Drain current		16.7		A
Gp	Power Gain	12			dB
△G	Gain Flatness	-0.8		+0.8	dB
PAE	Power Added Efficiency		60	-	%

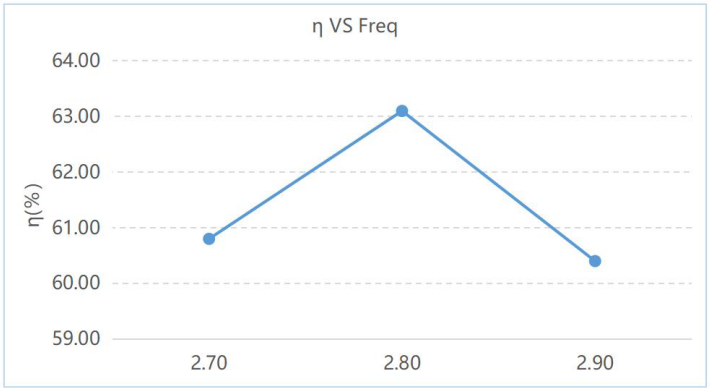
Test condition: Vd=50V, 10% duty, 1ms, Pin=45dBm; F: 2.7-2.9GHz.

Typical Performances

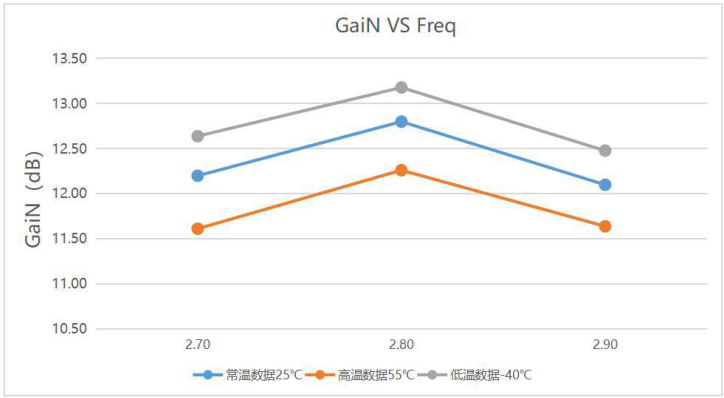
Pout



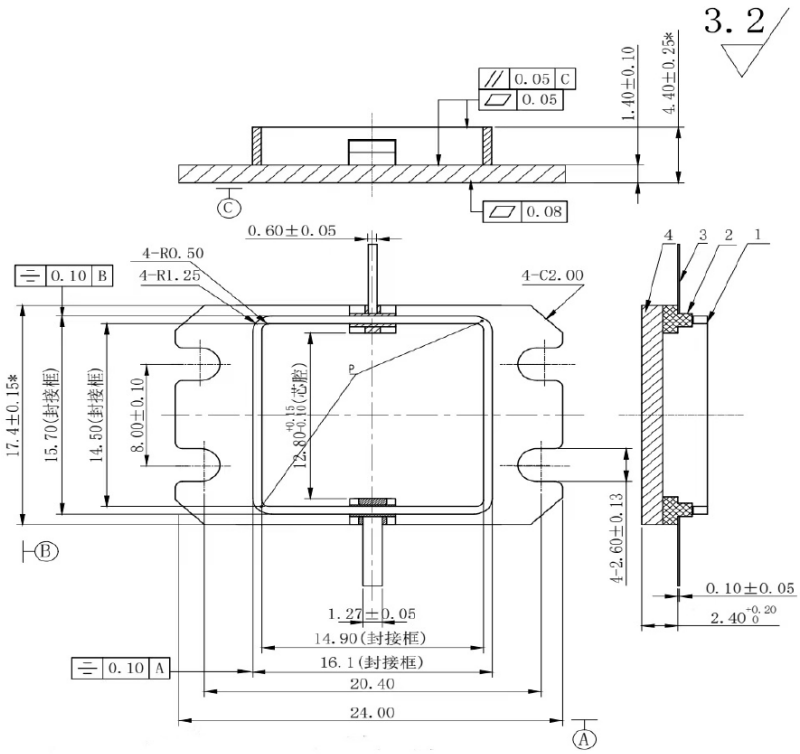
PAE



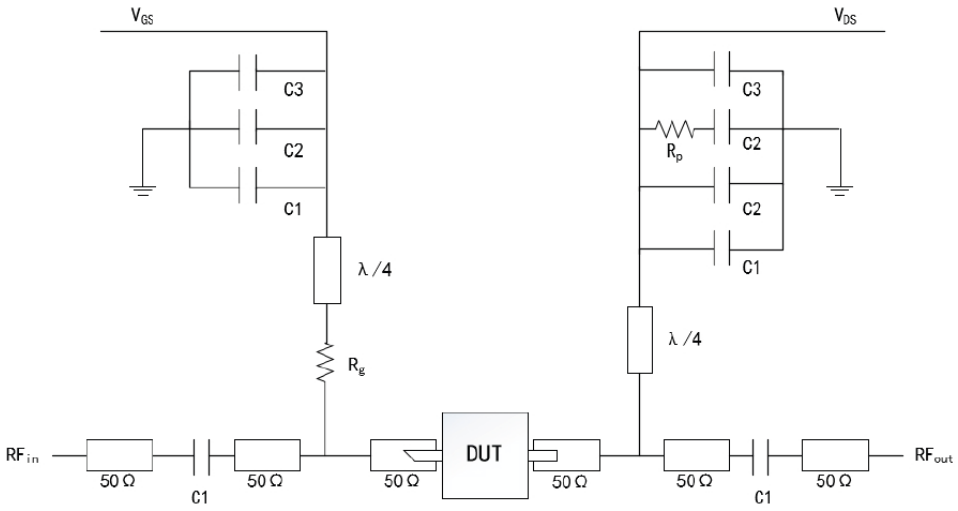
Gain



Dimension (Unit: mm)



Recommended Circuit



C1: 8pF C2: 1000pF C3: 100uF Rp: 51Ω Rg: 15Ω